

DMTH8008SPS-13 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number DMTH8008SPS-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMTH8008SPS-13

Description MOSFET N-CH 80V 92A PWRDI5060-8

Detailed Description N-Channel 80 V 92A (Tc) 1.6W (Ta), 100W (Tc) Surfa

ce Mount PowerDI5060-8



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMTH8008SPS-13	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
80 V	92A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
6V, 10V	7.8mOhm @ 14A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 1mA	34 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	1950 pF @ 40 V
FET Feature:	Power Dissipation (Max):
	1.6W (Ta), 100W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI5060-8	8-PowerTDFN
Base Product Number:	
DMTH8008	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D Tc = +25°C
80V	7.8mΩ @ V _{GS} = 10V	92A

Description and Applications

This new generation MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in power management and load switches.

- DC-DC converters
- Load switches

Features

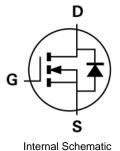
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (<u>DMTH8008SPSQ</u>)

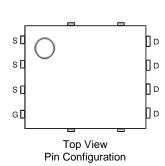
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 <a>®
- Weight: 0.097 grams (Approximate)

Site 1:

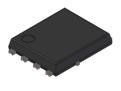






Site 2:

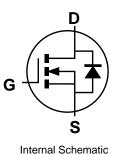
PowerDI5060-8/SWP (Type UX)

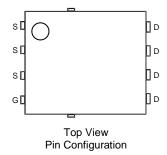


Top View



Bottom View





Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

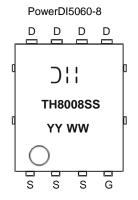


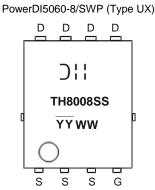
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	Fackage	Qty.	Carrier	
DMTH8008SPS-13	PowerDI5060-8	2500	Tape & Reel	
DWITH00083F3-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

Note:

Marking Information





⊃¦¦ = Manufacturer's Marking TH8008SS = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

Maximum Ratings (@Tc = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	80	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 5) Steady $T_C = +25^{\circ}C$ State $T_C = +100^{\circ}C$			lD	92 65	А
Maximum Continuous Body Diode Forward Current (Note 5)			Is	83	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	360	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	360	Α
Avalanche Current, L = 0.1mH (Note 6)			IAS	40	Α
Avalanche Energy, L = 0.1mH (Note 6)		Eas	80	mJ	

Thermal Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T _A = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	RөJA	95	°C/W
Total Power Dissipation (Note 8)	T _A = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	RөJA	44	°C/W
Total Power Dissipation (Note 5)	T _C = +25°C	P _D	100	W
Thermal Resistance, Junction to Case (Note 5)	·	Rejc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

- 5. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 7. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 8. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{4.} For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



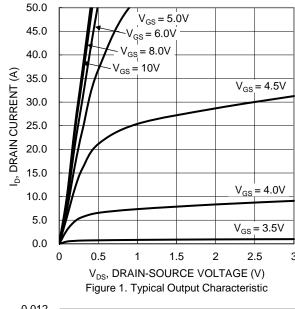
Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

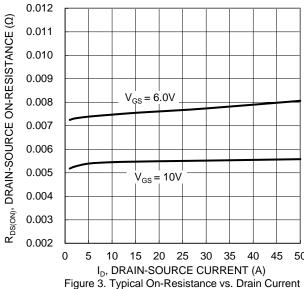
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	80	_	_	V	VGS = 0V, ID = 1mA	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 64V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	2	_	4	V	V _{DS} = V _{GS} , I _D = 1mA	
Static Drain-Source On-Resistance	D-s/s/s		6.5	7.8	mΩ	$V_{GS} = 10V, I_D = 14A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.8	11	11122	$V_{GS} = 6V, I_D = 12A$	
Diode Forward Voltage	VsD	_	0.8	1.2	V	V _G S = 0V, I _S = 14A	
DYNAMIC CHARACTERISTICS (Note 10)	DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	-	1950	_		V _{DS} = 40V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss		826		pF		
Reverse Transfer Capacitance	Crss		56	_			
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 6V)	Q_g	_	23	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	34	_	nC	\/ 40\/ I- 44A	
Gate-Source Charge	Qgs	_	6	_	nc	$V_{DS} = 40V, I_{D} = 14A$	
Gate-Drain Charge	Q_{gd}	_	12	_			
Turn-On Delay Time	tD(ON)	_	8	_			
Turn-On Rise Time	t _R	_	15	_	20	$V_{DD} = 40V, V_{GS} = 10V$	
Turn-Off Delay Time	tD(OFF)	_	29	_	ns	$I_D=14A,R_g=6\Omega$	
Turn-Off Fall Time	t _F	_	21	_			
Body Diode Reverse Recovery Time	trr	_	43	_	ns	1- 44A dl/dk 400A/	
Body Diode Reverse Recovery Charge	Q _{RR}	_	49	_	nC	Is = 14A, dI/dt = 100A/µs	

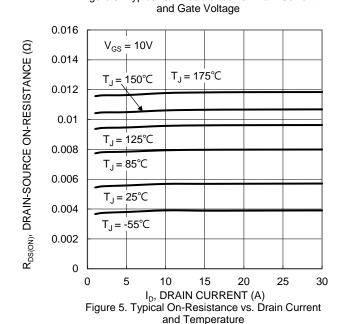
Notes:

^{9.} Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.









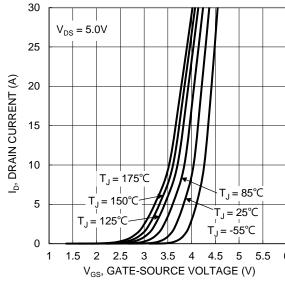
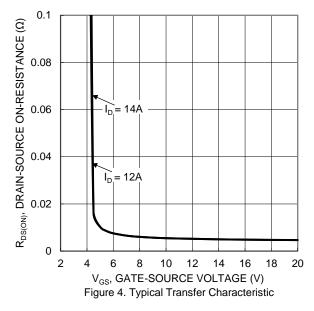
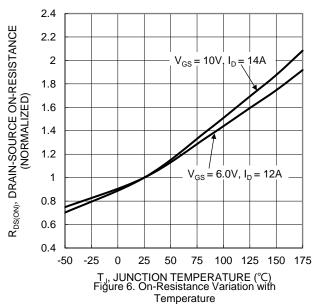


Figure 2. Typical Transfer Characteristic







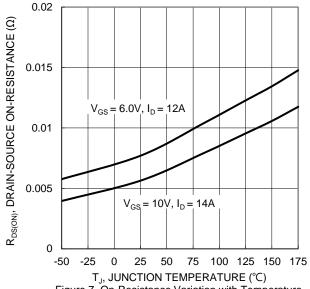


Figure 7. On-Resistance Variation with Temperature

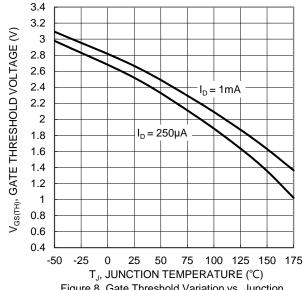
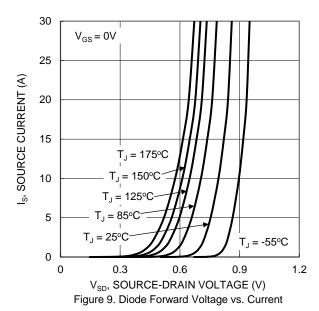
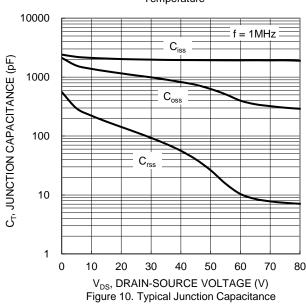


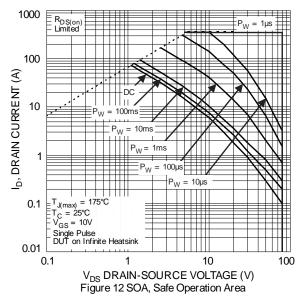
Figure 8. Gate Threshold Variation vs. Junction Temperature



10 8 6 $V_{GS}(V)$ 4 $V_{DS} = 40V, I_{D} = 14A$ 2 0 0 20 5 10 15 25 30 35 Q_q (nC)

Figure 11. Gate Charge





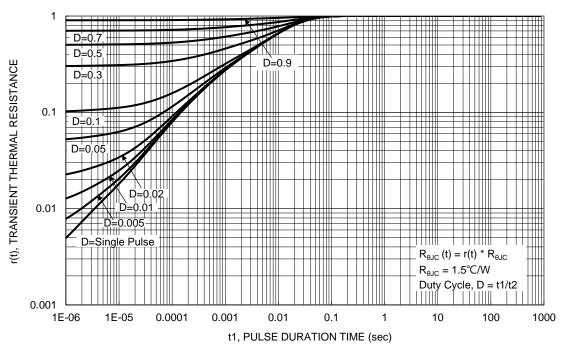


Figure 13. Transient Thermal Resistance

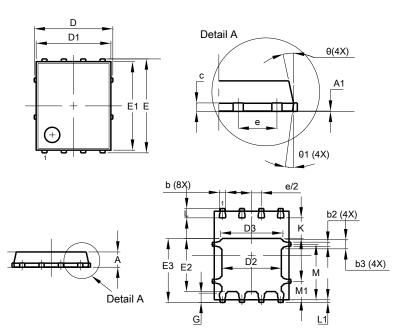


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

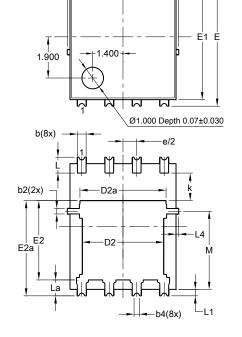
PowerDI5060-8

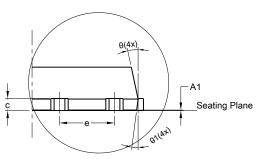


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
E	(6.15 BSC		
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC	;	
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

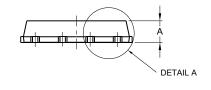
Site 2:

PowerDI5060-8/SWP (Type UX)





DETAIL A



PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A1	0	0.05	
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	C).25REF	-
С	0.230	0.330	0.277
D	5	.15 BS0	\sim
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6	.40 BS0	
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
е	1	.27BSC	
k	1.05		
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a 0.050REF			
L4	0.025	0.225	0.125
М	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

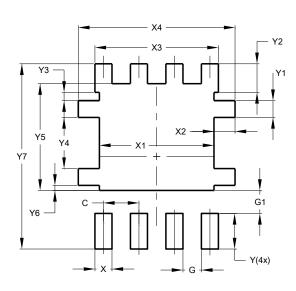


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

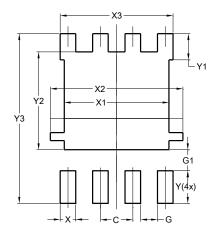
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. All other trademarks are the property of their respective owners.

© 2023 Diodes Incorporated. All Rights Reserved.

www.diodes.com



OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com